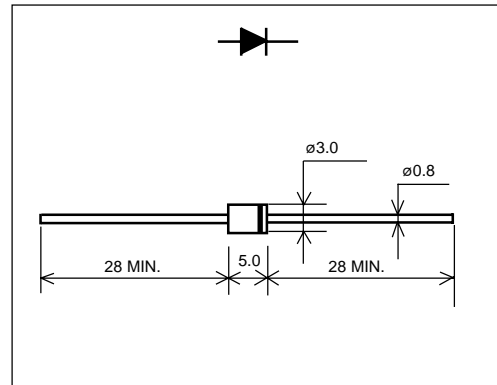


ERB44 (1.0A)

(200 to 1000V / 1.0A)

FAST RECOVERY DIODE

■ Outline drawings, mm



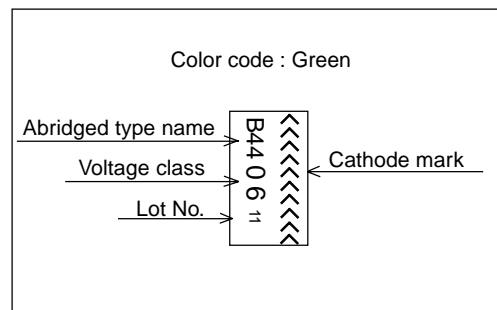
■ Features

- High voltage by mesa design
- High reliability

■ Applications

- High speed switching

■ Marking



■ Maximum ratings and characteristics

- Absolute maximum ratings

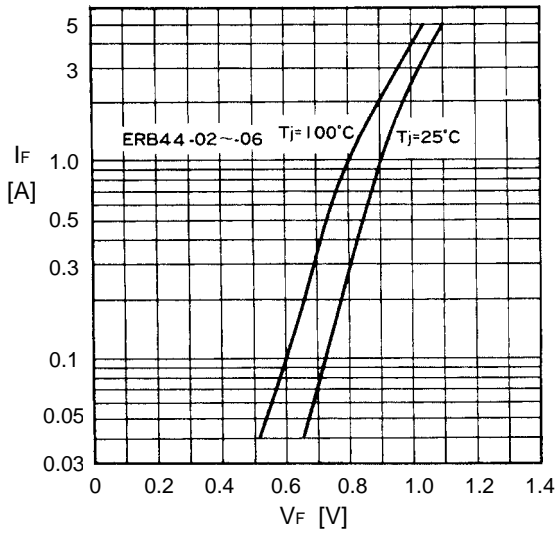
Item	Symbol	Conditions	Rating					Unit
			-02	-04	-06	-08	-10	
Repetitive peak reverse voltage	V_{RRM}		200	400	600	800	1000	V
Average forward current	$I_{F(AV)}$	Resistive load	1.0($T_a=40^\circ\text{C}$)				1.0($T_a=25^\circ\text{C}$)	A
Surge current	I_{FSM}	Sine wave 10ms	30					A
Operating junction temperature	T_j		-40 to +140					$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to +140					$^\circ\text{C}$

- Electrical characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

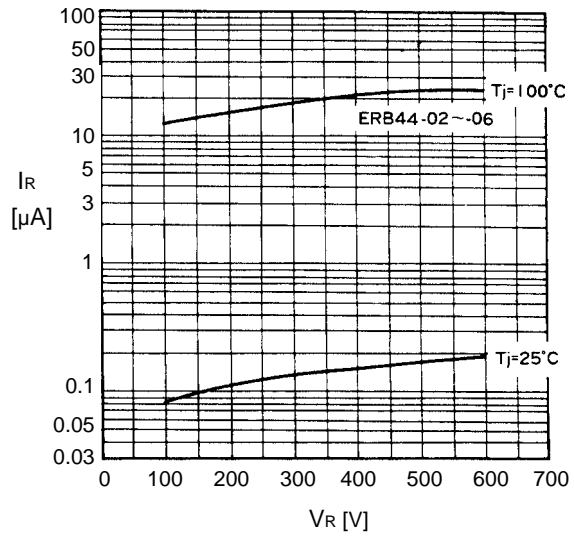
Item	Symbol	Conditions	Max.		Unit
			-02 to -08	-10	
Forward voltage drop	V_{FM}	$I_{FM}=1.0\text{A}$	1.1	1.5	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	10		μA
Reverse recovery time	t_{rr}	$I_F=0.1\text{A}, I_R=0.1\text{A}$	0.4		μs

■ Characteristics

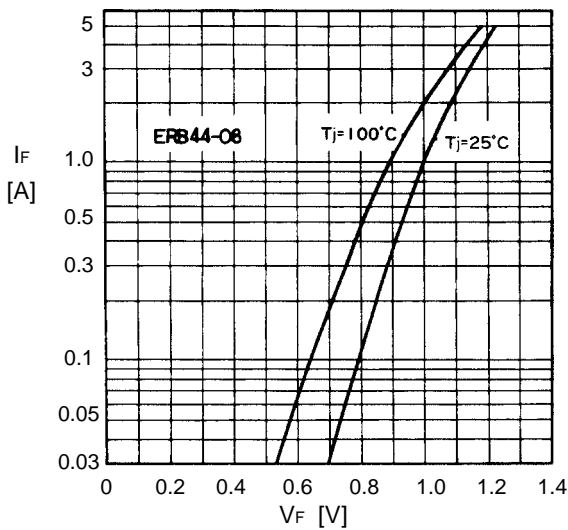
Forward characteristics



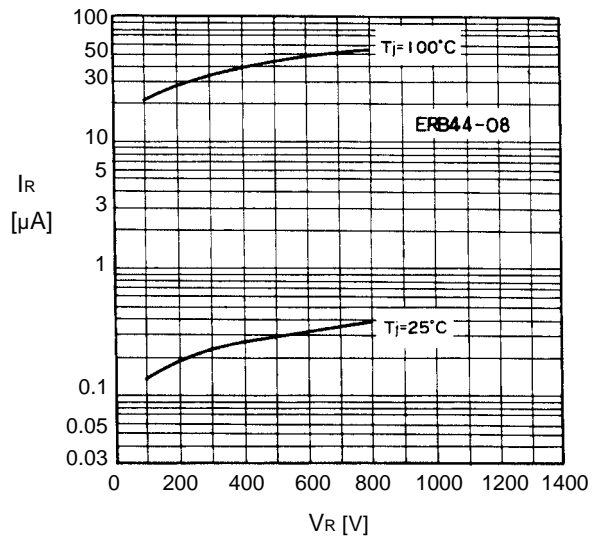
Reverse characteristics



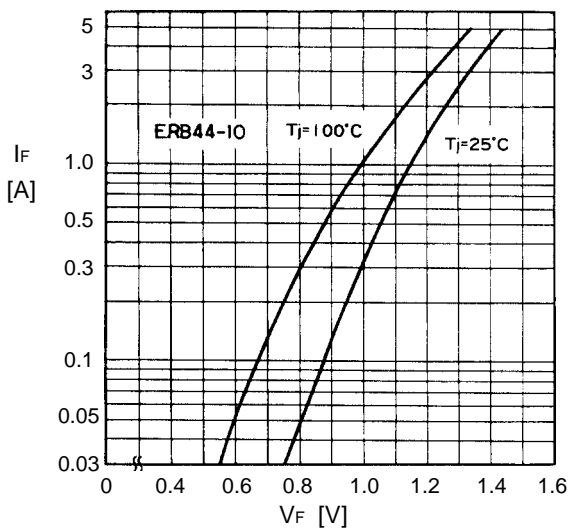
Forward characteristics



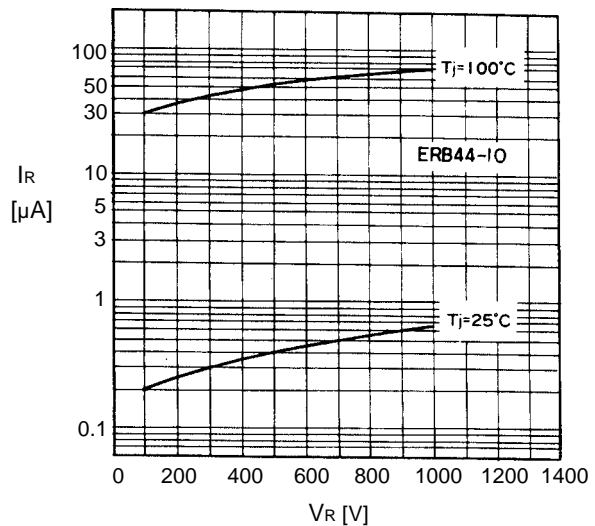
Reverse characteristics



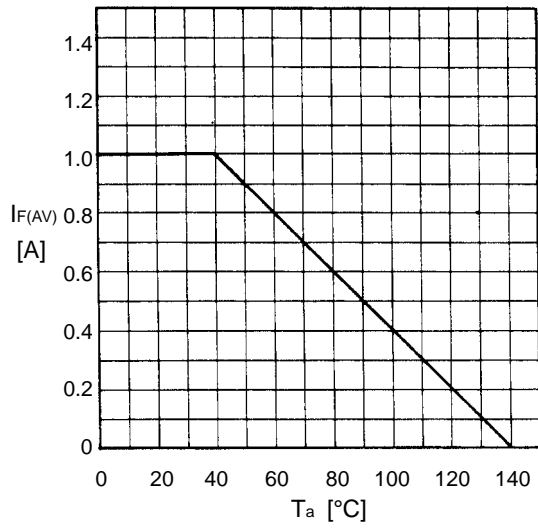
Forward characteristics



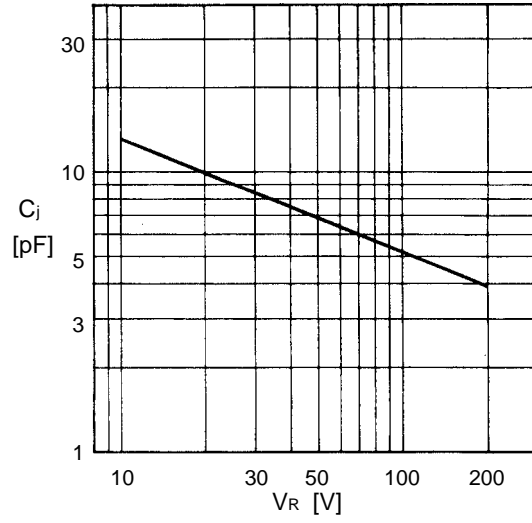
Reverse characteristics



Current derating ($I_{F(AV)}-T_a$)



Junction capacitance characteristics



Surge capability

